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Kind regards,

Team Nexperia



PNP resistor-equipped transistor; R1 = 100 kΩ, R2 = openRev. 1 — 2 July 2012Product data s

Product data sheet

1. **Product profile**

1.1 General description

PNP Resistor-Equipped Transistor (RET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package.

NPN complement: PDTC115TMB.

1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

1.3 Applications

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
lo	output current		-	-	-100	mA
R1	bias resistor 1 (input)	T _{amb} = 25 °C	70	100	130	kΩ



PNP resistor-equipped transistor; $R1 = 100 \text{ k}\Omega$, R2 = open

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		3
3	0	output (collector)	2 Transparent top view DFN1006B-3 (SOT883B)	1 2 sym009

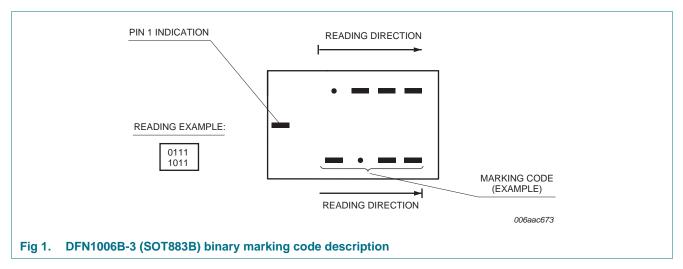
3. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PDTA115TMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B				

4. Marking

Table 4.	Marking codes
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Type number	Marking code
PDTA115TMB	0010 0001



PNP resistor-equipped transistor; $R1 = 100 \text{ k}\Omega$, R2 = open

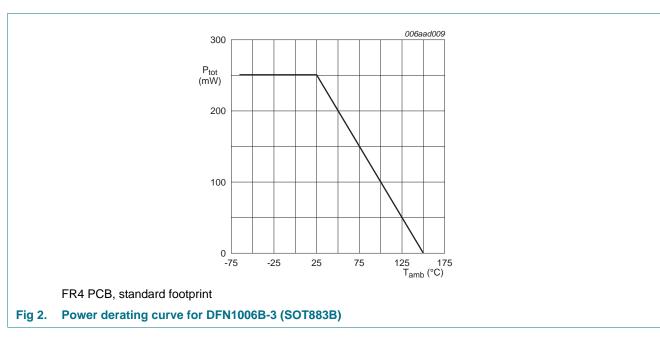
5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions		Min	Max	Unit
collector-base voltage	open emitter		-	-50	V
collector-emitter voltage	open base		-	-50	V
emitter-base voltage	open collector		-	-5	V
output current			-	-100	mA
peak collector current	pulsed; t _p ≤ 1 ms		-	-100	mA
total power dissipation	T _{amb} ≤ 25 °C	<u>[1]</u>	-	250	mW
junction temperature			-	150	°C
ambient temperature			-65	150	°C
storage temperature			-65	150	°C
	collector-base voltagecollector-emitter voltageemitter-base voltageoutput currentpeak collector currenttotal power dissipationjunction temperatureambient temperature	collector-base voltageopen emittercollector-emitter voltageopen baseemitter-base voltageopen collectoroutput currentpulsed; $t_p \le 1 \text{ ms}$ peak collector currentpulsed; $t_p \le 1 \text{ ms}$ total power dissipation $T_{amb} \le 25 \text{ °C}$ junction temperatureambient temperature	collector-base voltageopen emittercollector-emitter voltageopen baseemitter-base voltageopen collectoroutput currentoutput currentpeak collector currentpulsed; $t_p \le 1$ mstotal power dissipation $T_{amb} \le 25 \text{ °C}$ junction temperature[1]ambient temperature	collector-base voltageopen emitter-collector-emitter voltageopen base-emitter-base voltageopen collector-output currentopen collector-peak collector currentpulsed; $t_p \le 1 \text{ ms}$ -total power dissipation $T_{amb} \le 25 \text{ °C}$ [1]junction temperatureambient temperature-65	collector-base voltage open emitter - -50 collector-emitter voltage open base - -50 emitter-base voltage open collector - -5 output current - -100 peak collector current pulsed; $t_p \le 1 \text{ ms}$ - -100 total power dissipation $T_{amb} \le 25 \text{ °C}$ 11 - 250 junction temperature - 150 - -

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u>	-	-	500	K/W

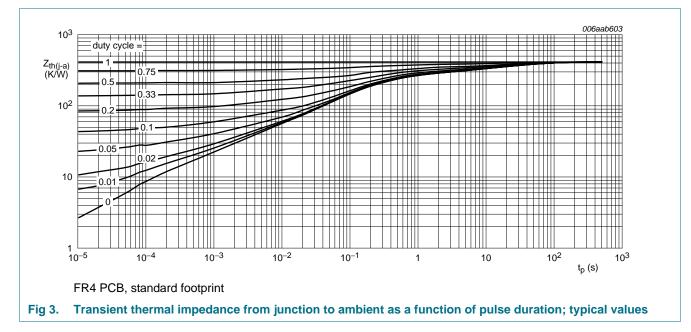
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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PDTA115TMB

PNP resistor-equipped transistor; $R1 = 100 \text{ k}\Omega$, R2 = open



7. Characteristics

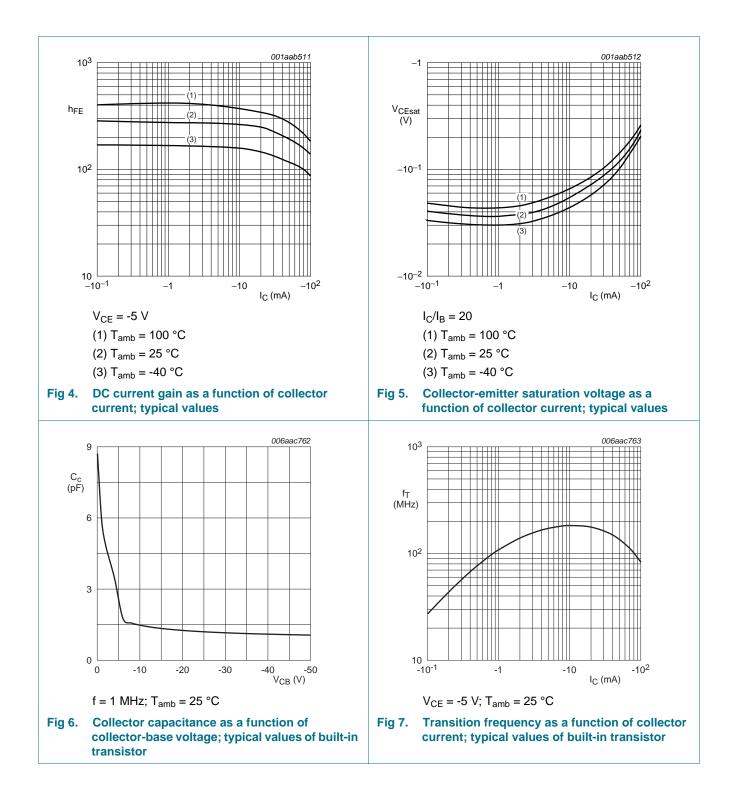
Table 7.Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	V_{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
I _{CEO}	collector-emitter cut-off	V_{CE} = -30 V; I _B = 0 A; T _{amb} = 25 °C	-	-	-1	μA
	current	V_{CE} = -30 V; I _B = 0 A; T _j = 150 °C	-	-	-5	μA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_C = -1 mA; T_{amb} = 25 °C	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_{C} = -5 \text{ mA}; I_{B} = -0.25 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	-150	mV
R1	bias resistor 1 (input)	T _{amb} = 25 °C	70	100	130	kΩ
C _C	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; \text{ I}_{C} = -10 \text{ mA}; \text{ f} = 100 \text{ MHz};$ $I'_{amb} = 25 \text{ °C}$	1 -	180	-	MH

[1] Characteristics of built-in transistor.

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PNP resistor-equipped transistor; R1 = 100 k Ω , R2 = open



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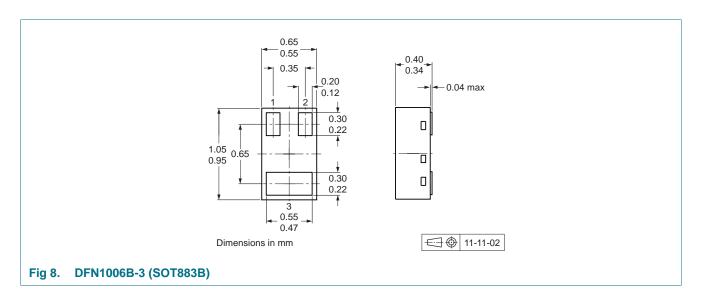
PNP resistor-equipped transistor; $R1 = 100 \text{ k}\Omega$, R2 = open

8. Test information

8.1 Quality information

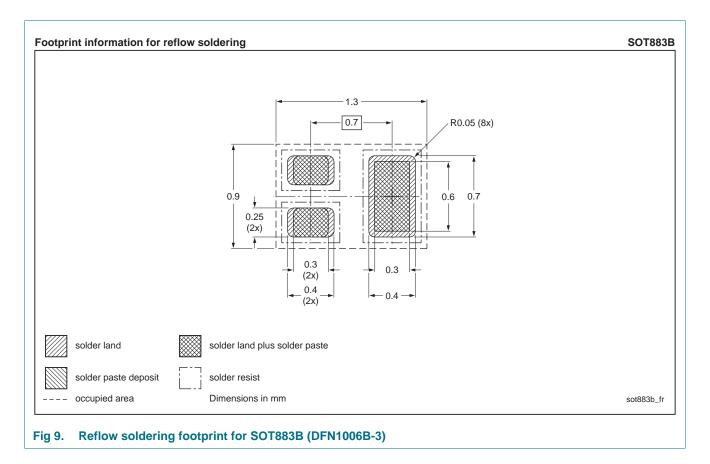
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



PNP resistor-equipped transistor; $R1 = 100 \text{ k}\Omega$, R2 = open

10. Soldering



PNP resistor-equipped transistor; R1 = 100 k Ω , R2 = open

11. Revision history

Table 8. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA115TMB v.1	20120702	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1] [2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Product data sheet

PDTA115TMB

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PNP resistor-equipped transistor; $R1 = 100 \text{ k}\Omega$, R2 = open

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